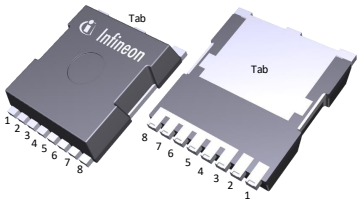
SiC MOSFET

CoolSiC™ MOSFET 650 V G2

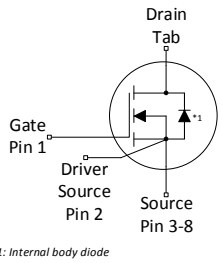
TOLL



Built on Infineon's robust 2nd generation Silicon Carbide trench technology, the 650 V CoolSiC™ MOSFET delivers unparalleled performance, superior reliability, and great ease of use. It enables cost effective, highly efficient, and simplified designs to fulfill the ever-growing system and market needs.

Features

- Ultra-low switching losses
- Benchmark gate threshold voltage, $V_{GS(th)}$ = 4.5 V
- Robust against parasitic turn-on even with 0 V turn-off gate voltage
- Flexible driving voltage and compatible with bipolar driving scheme
- Robust body diode operation under hard commutation events
- .XT interconnection technology for best-in-class thermal performance



*1: Internal body diode

Benefits

- Enables high efficiency and high power density designs
- Facilitates great ease of use and integration
- Provides the best price performance ratio compared to Industry's most ambitious roadmaps
- Reduces the size, weight and bill of materials of the systems
- Enhances system robustness and reliability

Potential applications

- SMPS
- Solar PV inverters
- Energy storage and battery formation
- UPS
- EV charging infrastructure
- Motor drives

Product validation

Fully qualified according to JEDEC for Industrial Applications

Please note: The source and driver source pins are not exchangeable. Their exchange might lead to malfunction.

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DSS} over full $T_{j,range}$	650	V
$R_{DS(on),typ}$	10.0	mΩ
$R_{DS(on),max}$	13.1	mΩ
$Q_{G,typ}$	113	nC
$I_{D,pulse}$	575	A
Q_{oss} @ 400 V	212	nC
E_{oss} @ 400 V	28.8	µJ

Part number	Package	Marking	Related links
IMT65R010M2H	PG-HSOF-8	65R010M2	see Appendix A

Table of contents

1 Maximum ratings

at T_j = 25°C, unless otherwise specified.

Note: for optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous DC drain current [1]	I_{DDC}	-	-	168 126	A	T_c = 25°C T_c = 100°C
Peak drain current [2]	I_{DM}	-	-	575	A	T_c = 25°C, V_{GS} = 18 V
Avalanche energy, single pulse	E_{AS}	-	-	534	mJ	I_D = 20 A, V_{DD} = 50 V; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	2.67	mJ	
Avalanche current, single pulse	I_{AS}	-	-	20.0	A	-
MOSFET *dv/dt* ruggedness	*dv/dt*	-	-	200	V/ns	V_{DS}= 0...400 V
Gate source voltage (static) [3]	V_{GS}	-7	-	23	V	-
Gate source voltage (transient)	V_{GS}	-10	-	25	V	t_p ≤ 500 ns, duty cycle ≤ 1%
Power dissipation	P_{tot}	-	-	681	W	T_c = 25°C
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature	T_j	-55	-	175	°C	
Mounting torque	-	-	-	n.a.	Ncm	
Continuous reverse drain current [1]	I_{SDC}	-	-	168 121	A	V_{GS} = 18 V, T_c = 25°C V_{GS} = 0 V, T_c = 25°C
Peak reverse drain current [2]	I_{SM}	-	-	575 173	A	T_c = 25°C, t_p ≤ 250 ns T_c = 25°C
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms}, T_c = 25°C, t = 1 min

1) Limited by $T_{j,max}$.

2) Pulse width t_{pulse} limited by $T_{j,max}$.

3) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{th(j-c)}$	-	-	0.22	°C/W	Not subject to production test. Parameter verified by design/characterization according to JESD51-14.
Soldering temperature, reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL3

3 Operating range

Table 4 Operating range

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Recommended turn-on voltage	$V_{GS(on)}$	-	18	-	V	-
Recommended turn-off voltage	$V_{GS(off)}$	-	0	-	V	

4 Electrical characteristics

at T_j = 25°C, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source voltage	V_{DSS}	650	-	-	V	V_{GS} = 0 V, I_D = 1.87 mA
Gate threshold voltage [4]	$V_{GS(th)}$	3.5	4.5	5.6	V	V_{DS} = V_{GS}, I_D = 18.7 mA
Zero gate voltage drain current	I_{DSS}	-	1 3	75 -	µA	V_{DS} = 650 V, V_{GS} = 0 V, T_j = 25°C V_{DS} = 650 V, V_{GS} = 0 V, T_j = 175°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS} = 20 V, V_{DS} = 0 V
Drain-source on-state resistance	$R_{DS(on)}$	-	13.0 10.0 9.1 16	- 13.1 - -	mΩ	V_{GS} = 15 V, I_D = 92.1 A, T_j = 25°C V_{GS} = 18 V, I_D = 92.1 A, T_j = 25°C V_{GS} = 20 V, I_D = 92.1 A, T_j = 25°C V_{GS} = 18 V, I_D = 92.1 A, T_j =175°C
Internal gate resistance	$R_{G,int}$	-	1.7	-	Ω	f = 1 MHz

[4] Tested after 1 ms pulse at V_{GS} = +20 V. “Linear mode” operation is not recommended. For assessment of potential “linear mode” operation, please contact Infineon sales office.

Table 6 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.
Stray inductances and coupling capacitances must be minimized.
For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4001	-	pF	V_{GS} = 0 V, V_{DS} = 400 V, f = 250 kHz
Reverse transfer capacitance	C_{rss}	-	22	-	pF	
Output capacitance [5]	C_{oss}	-	297	386	pF	
Output charge [5]	Q_{oss}	-	212	276	nC	calculation based on C_{oss}
Effective output capacitance, energy related [6]	$C_{o(er)}$	-	359	-	pF	V_{GS} = 0 V, V_{DS} = 0...400 V
Effective output capacitance, time related [7]	$C_{o(tr)}$	-	531	-	pF	I_D = constant, V_{GS} = 0 V, V_{DS} = 0... 400 V
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	V_{DD} = 400 V, V_{GS} = 0/18 V, I_D = 92.1 A, $R_{G,ext}$ = 3.3 Ω; see table 10
Rise time	t_r	-	24	-	ns	
Turn-off delay time	$t_{d(off)}$	-	30	-	ns	
Fall time	t_f	-	9.4	-	ns	

Table 6 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.
Stray inductances and coupling capacitances must be minimized.
For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Turn-ON switching losses [8]	E_{on}	-	216	-	µJ	V_{DD} = 400 V, V_{GS} = 0/18 V, I_D = 92.1 A, $R_{G,ext}$ = 3.3 Ω
Turn-OFF switching losses [8]	E_{off}	-	371	-	µJ	
Total switching losses [8]	E_{tot}	-	587	-	µJ	

[5] Maximum specification is defined by calculated six sigma upper confidence bound.

[6] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V.

[7] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V.

[8] Values for 4-pin configuration based on TO-263-7 measurements; MOSFET used in half-bridge configuration without external diode.

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Plateau gate to source charge	$Q_{GS(pl)}$	-	29	-	nC	V_{DD} = 400 V, I_D = 92.1 A, V_{GS} = 0 to 18 V
Gate to drain charge	Q_{GD}	-	21	-	nC	
Total gate charge	Q_G	-	113	-	nC	

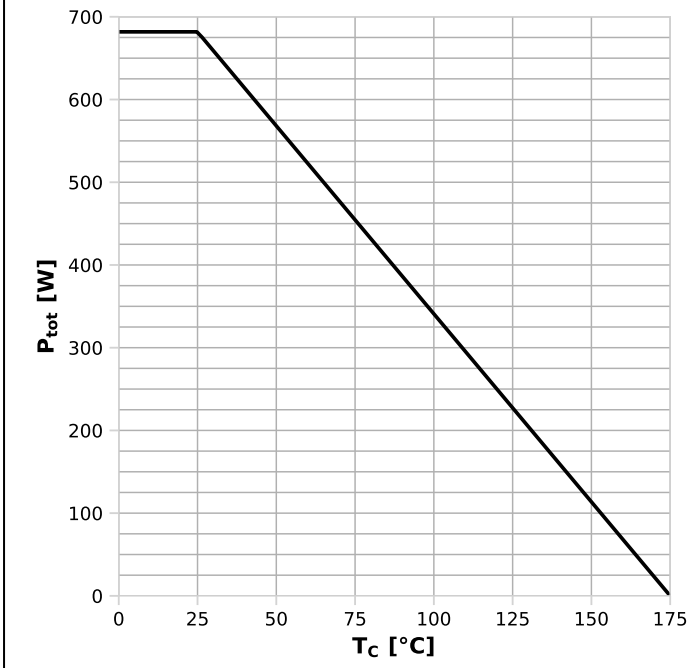
Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source reverse voltage	V_{SD}	-	4.3	-	V	V_{GS} = 0 V, I_S = 92.1 A, T_j = 25°C
MOSFET forward recovery time	t_{fr}	-	25 19	-	ns	V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 1000 A/µs; see table 9 V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 4000 A/µs; see table 9
MOSFET forward recovery charge [9]	Q_{fr}	-	224 376	-	nC	V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 1000 A/µs; see table 9 V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 4000 A/µs; see table 9
MOSFET peak forward recovery current	I_{frm}	-	18 40	-	A	V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 1000 A/µs; see table 9 V_{DD} = 400 V, I_S = 92.1 A, di_S/dt = 4000 A/µs; see table 9

[9] Q_{fr} includes Q_{oss}.

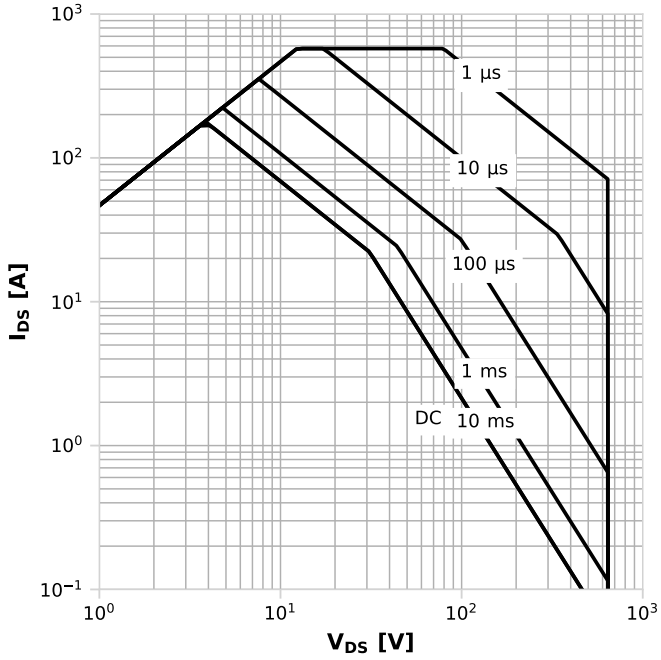
5 Electrical characteristics diagrams

Diagram 1: Power dissipation



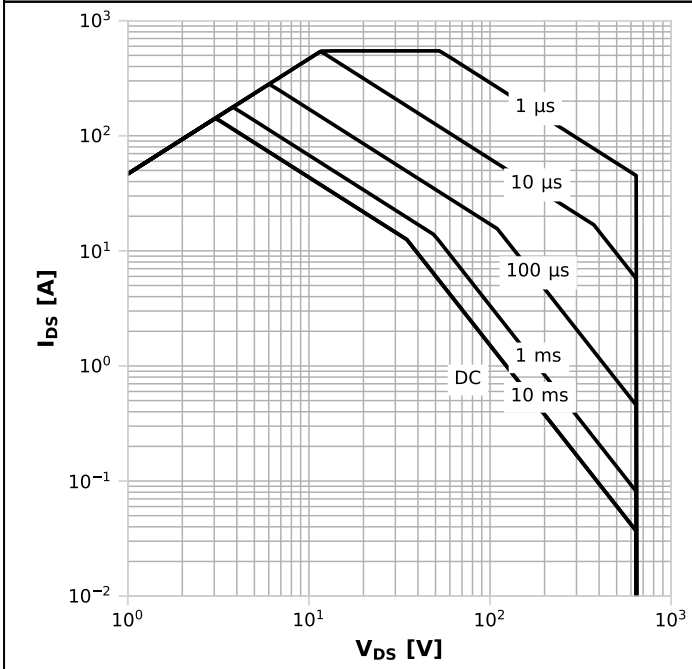
$P_{tot}=f(T_C)$

Diagram 2: Safe operating area



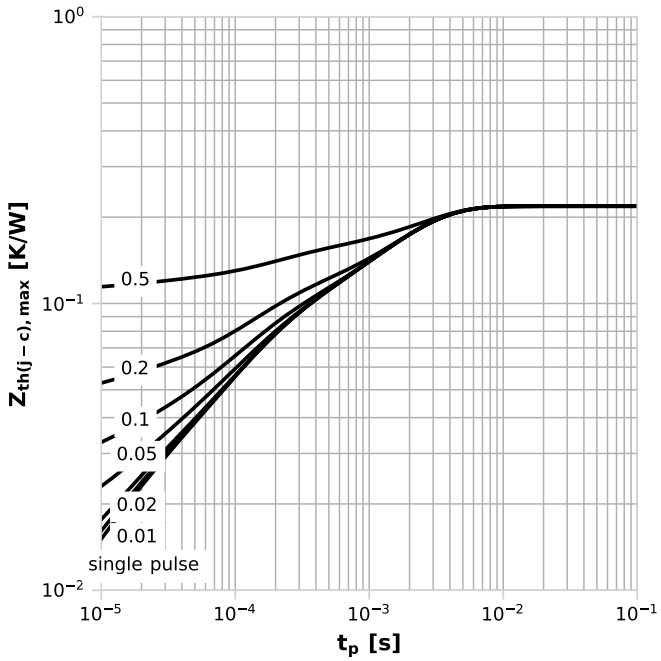
$I_{DS}=f(V_{DS})$; T_C=25 °C; D=0; parameter: t_p

Diagram 3: Safe operating area



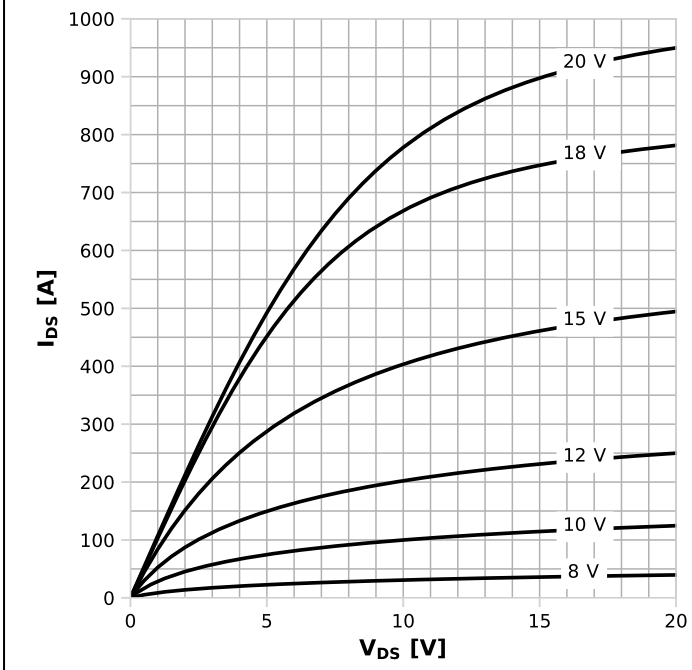
$I_{DS}=f(V_{DS})$; T_C=80 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



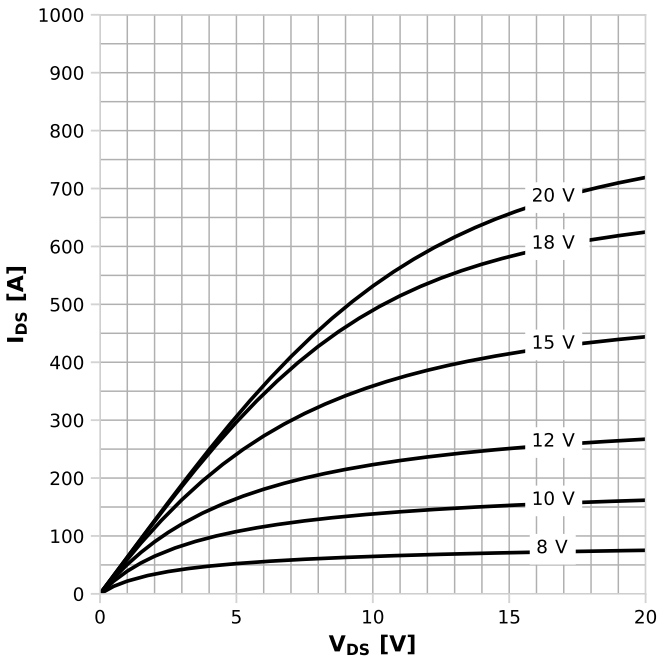
$Z_{th(j-c),max}=f(t_P)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



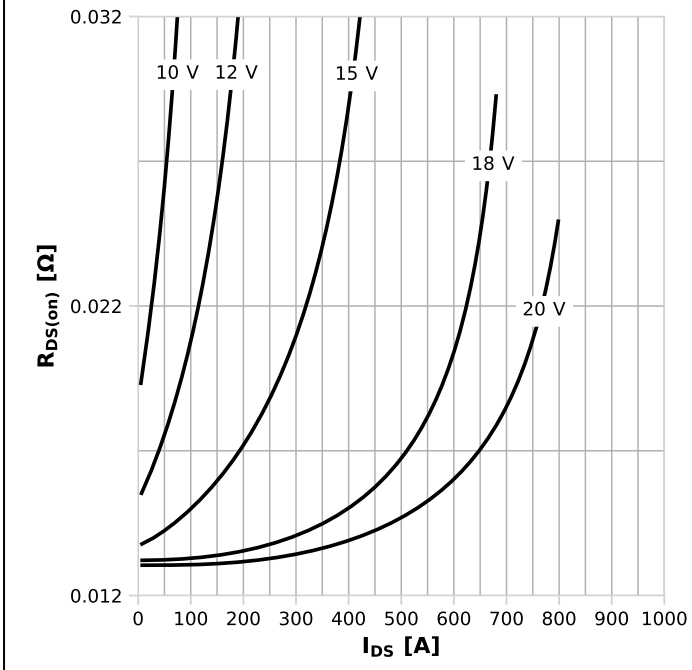
$I_{DS}=f(V_{DS})$; T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



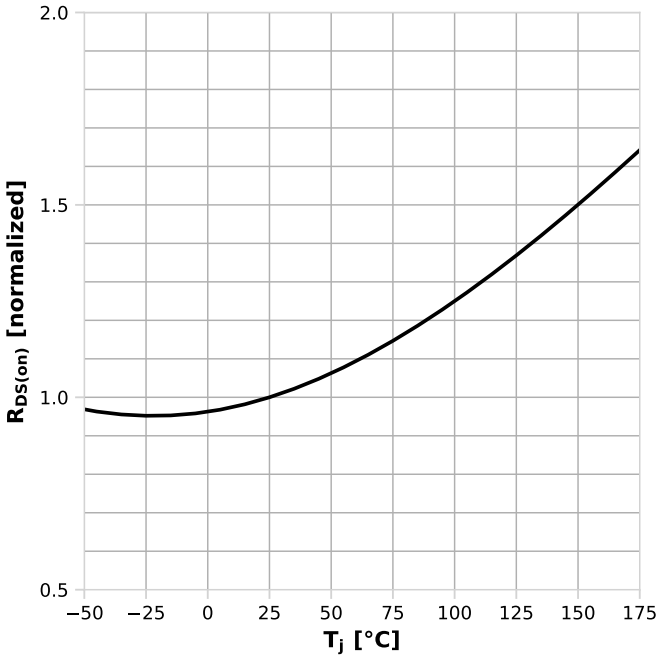
$I_{DS}=f(V_{DS})$; T_j=175 °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_{DS})$; T_j=125 °C; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



$R_{DS(on)}=f(T_j)$; I_D=92.1 A; V_{GS}=18 V

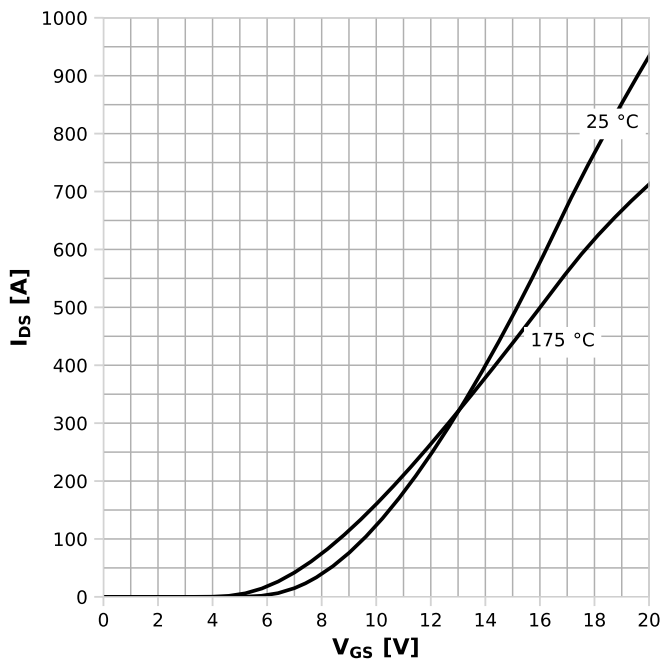
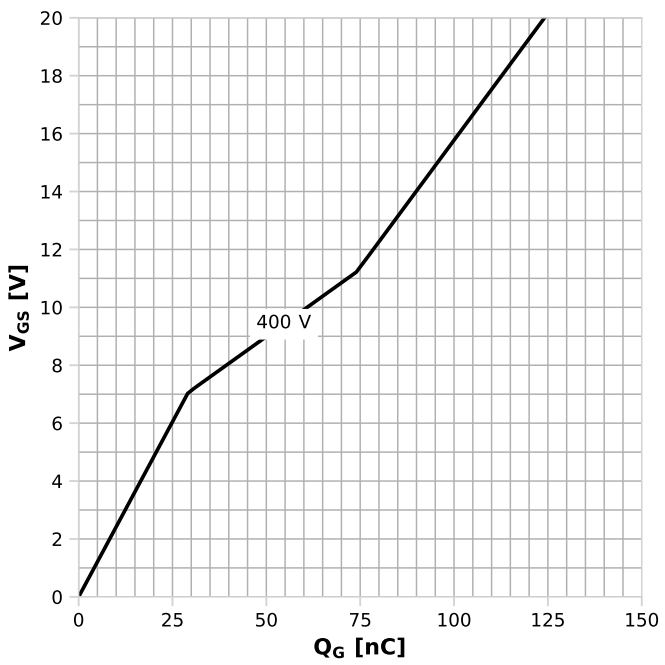
Diagram 9: Typ. transfer characteristics	Diagram 10: Typ. gate charge
	
$I_{DS}=f(V_{GS})$; V_{DS}=20 V; parameter: T_j	$V_{GS}=f(Q_G)$; I_D=92.1 A pulsed; parameter: V_{DD}

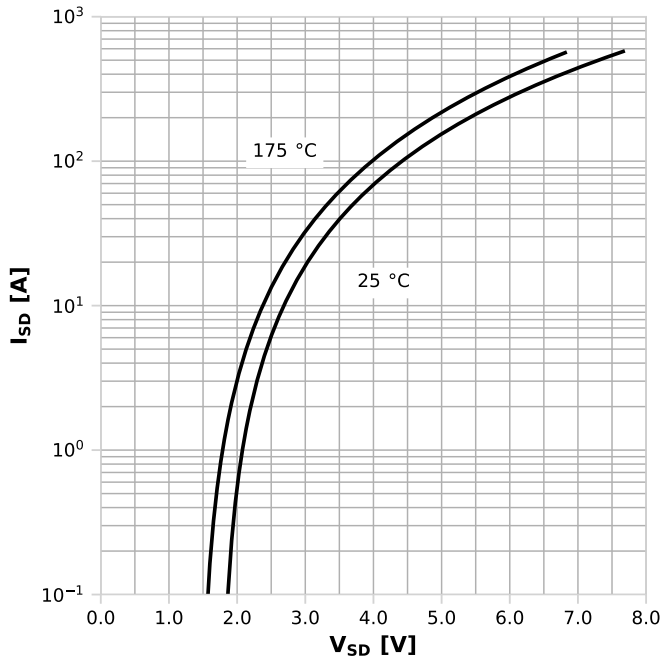
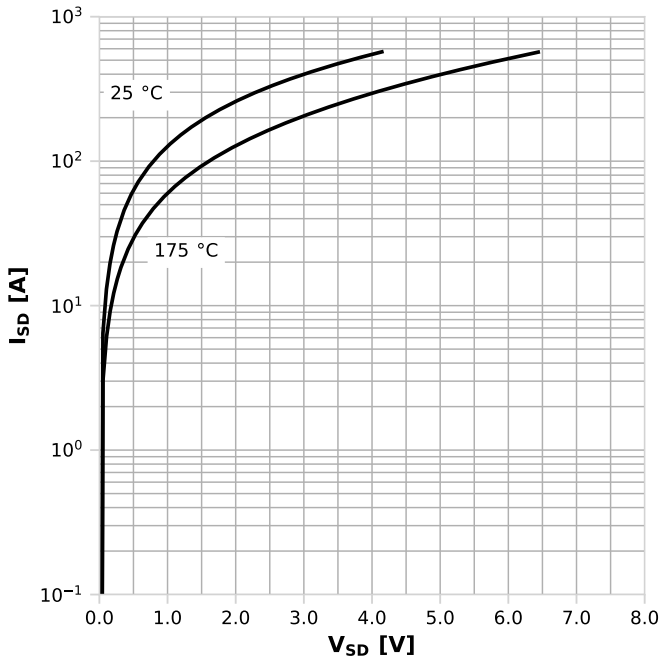
Diagram 11: Typ. reverse drain current characteristics	Diagram 12: Typ. reverse drain current characteristics
	
$I_{SD}=f(V_{SD})$; V_{GS}=0 V; parameter: T_j	$I_{SD}=f(V_{SD})$; V_{GS}=18 V; parameter: T_j

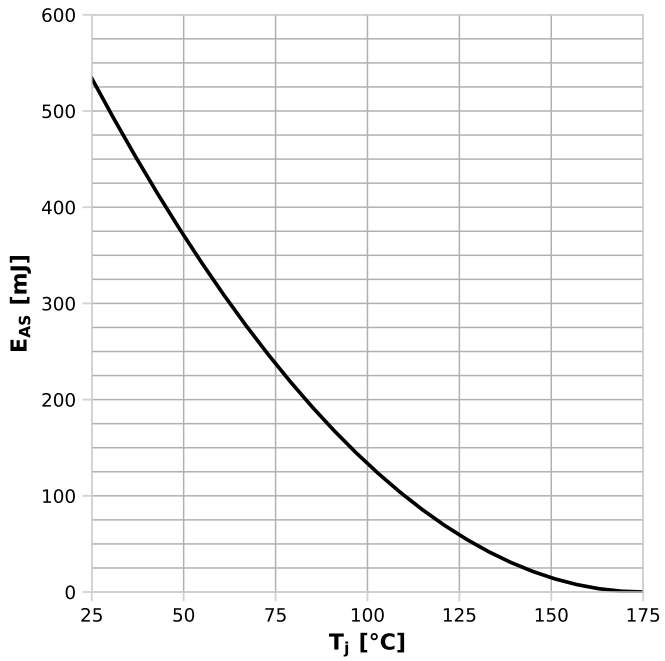
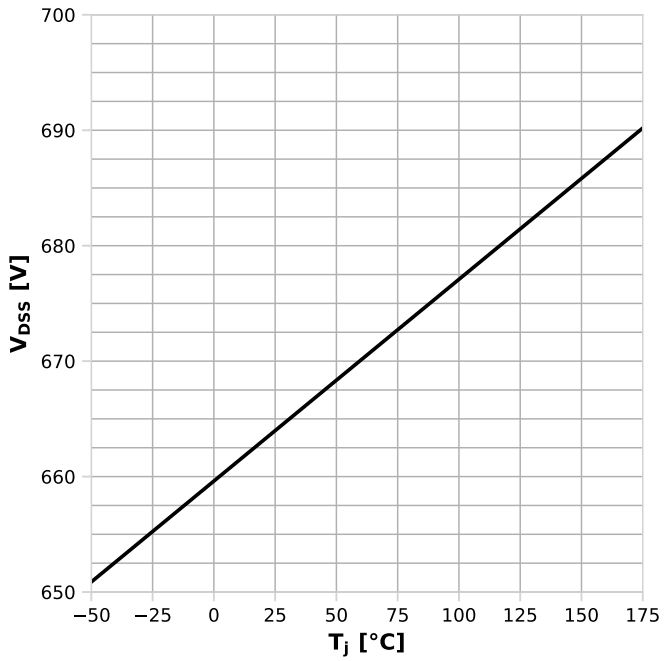
Diagram 13: Avalanche energy	Diagram 14: Drain-source breakdown voltage
	
$E_{AS}=f(T_j)$; I_D=20.0 A; V_{DD}=50 V	$V_{DSS}=f(T_j)$; I_D=1.87 mA

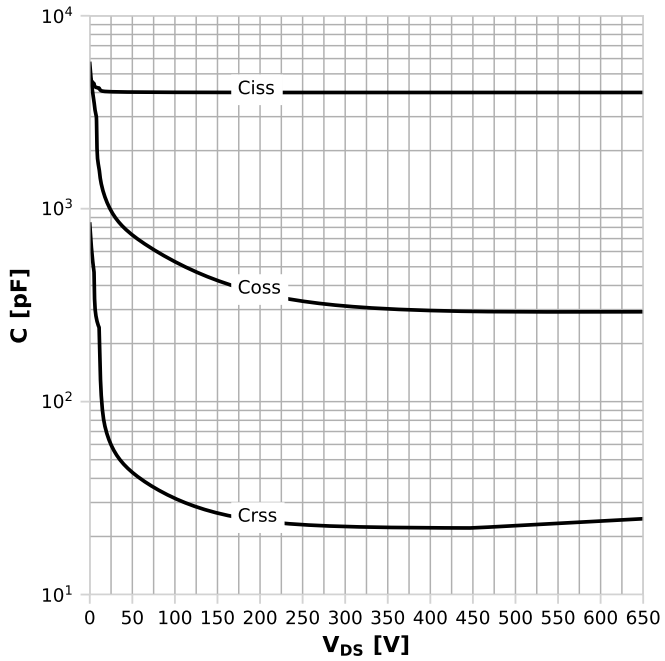
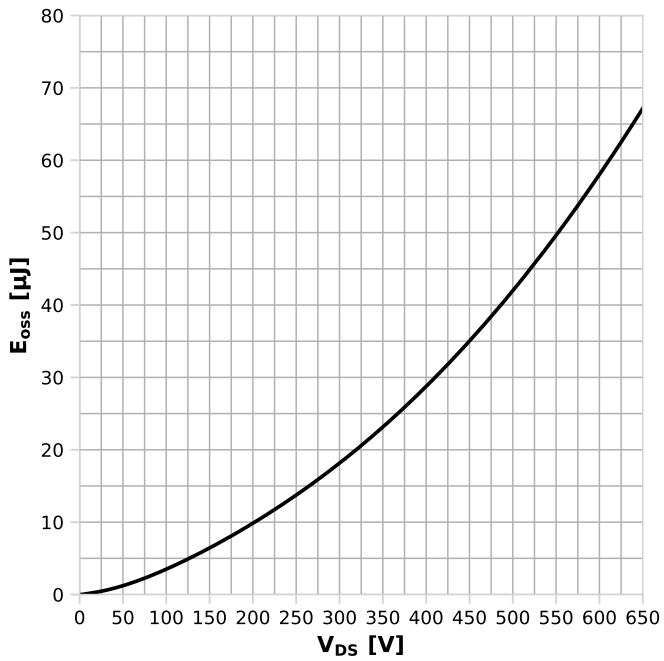
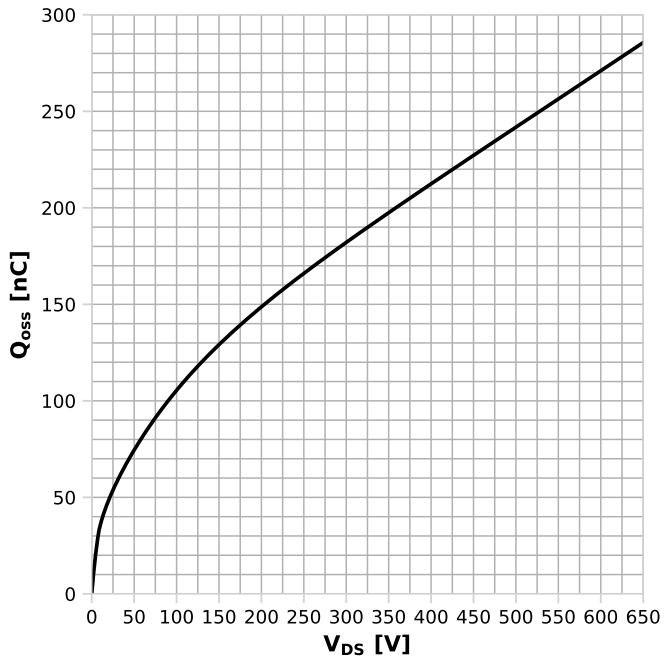
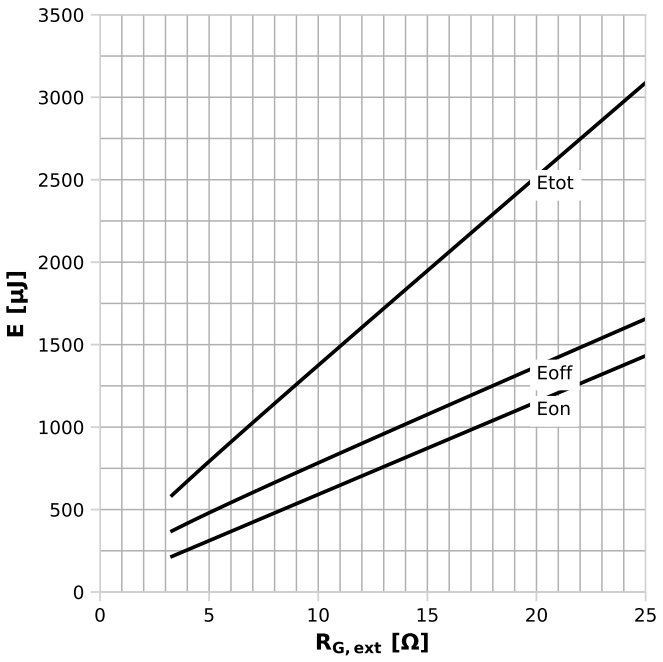
Diagram 15: Typ. capacitances	Diagram 16: Typ. Coss stored energy
	
C=f(V_{DS}); V_{GS}=0 V; f=250 kHz	$E_{oss}=f(V_{DS})$

Diagram 17: Typ. Qoss output charge



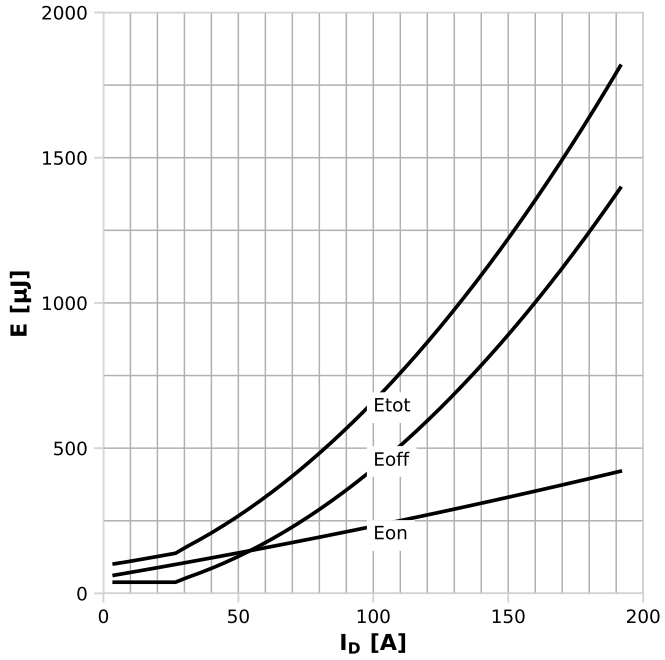
$Q_{oss}=f(V_{DS})$

Diagram 18: Typ. Switching Losses vs $R_{G,ext}$



$E=f(R_{G,ext})$; V_{DD}=400 V; V_{GS}=0-18 V; I_D=92.1 A

Diagram 19: Typ. Switching Losses vs switching current



$E=f(I_D)$; V_{DD}=400 V; V_{GS}=0-18 V; $R_{G,ext}$=3.3 Ω

6 Test circuits

Table 9 Body diode characteristics

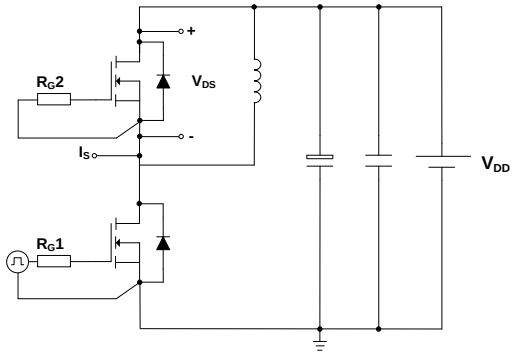
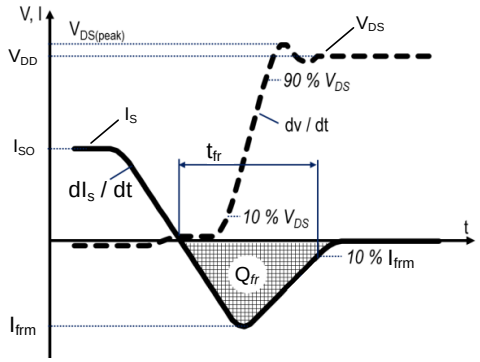
Test circuit for body diode characteristics	Body diode recovery waveform
	

Table 10 Switching times

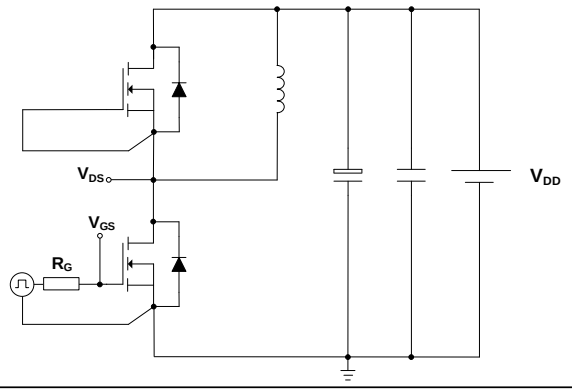
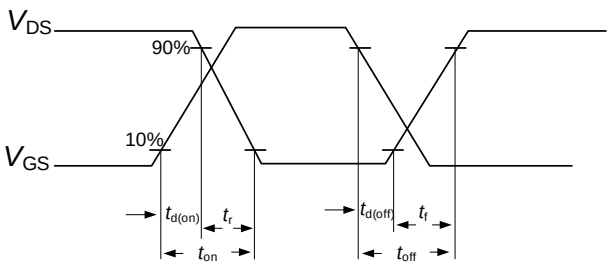
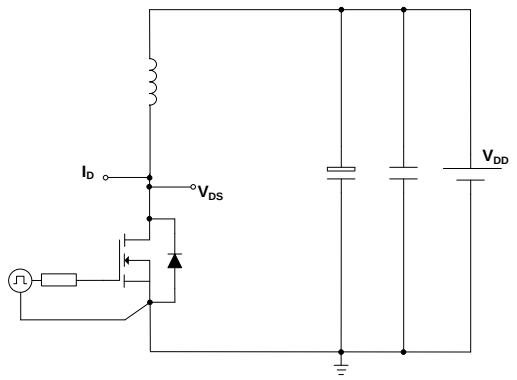
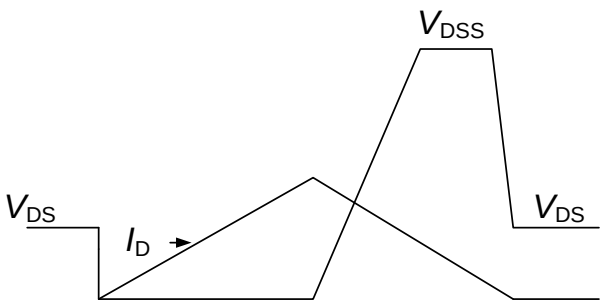
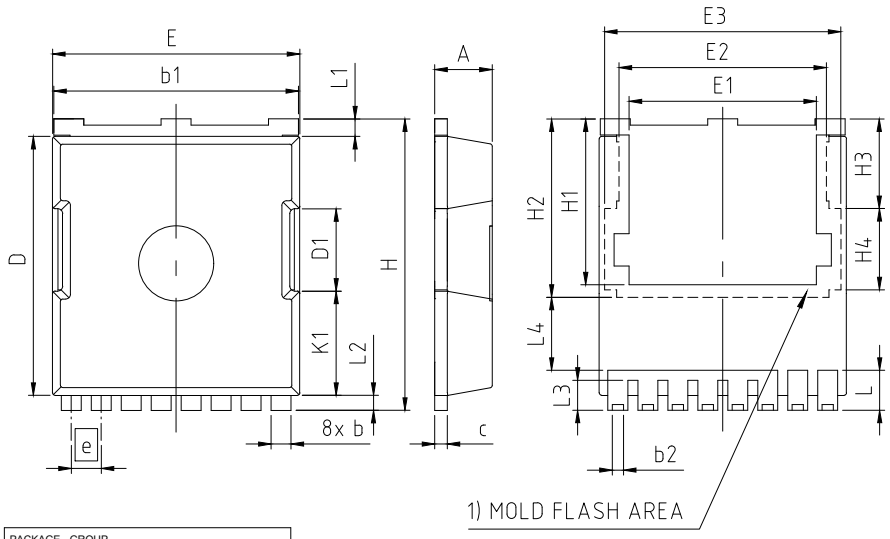
Switching times test circuit for inductive load	Switching times waveform
	

Table 11 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package outlines



PACKAGE - GROUP NUMBER:	PG-HSOF-8-U02	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D1	3.30	
E	9.70	10.10
E1	7.50	
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.88
H1	6.55	6.95
H2	7.15	
H3	3.59	
H4	3.26	
N	8	
K1	4.18	
L	1.40	1.80
L1	0.50	0.90
L2	0.50	0.70
L3	1.00	1.30
L4	2.62	2.81

1) PARTIALLY COVERED WITH MOLD FLASH

Figure 1 Outline PG-HSOF-8, dimensions in mm

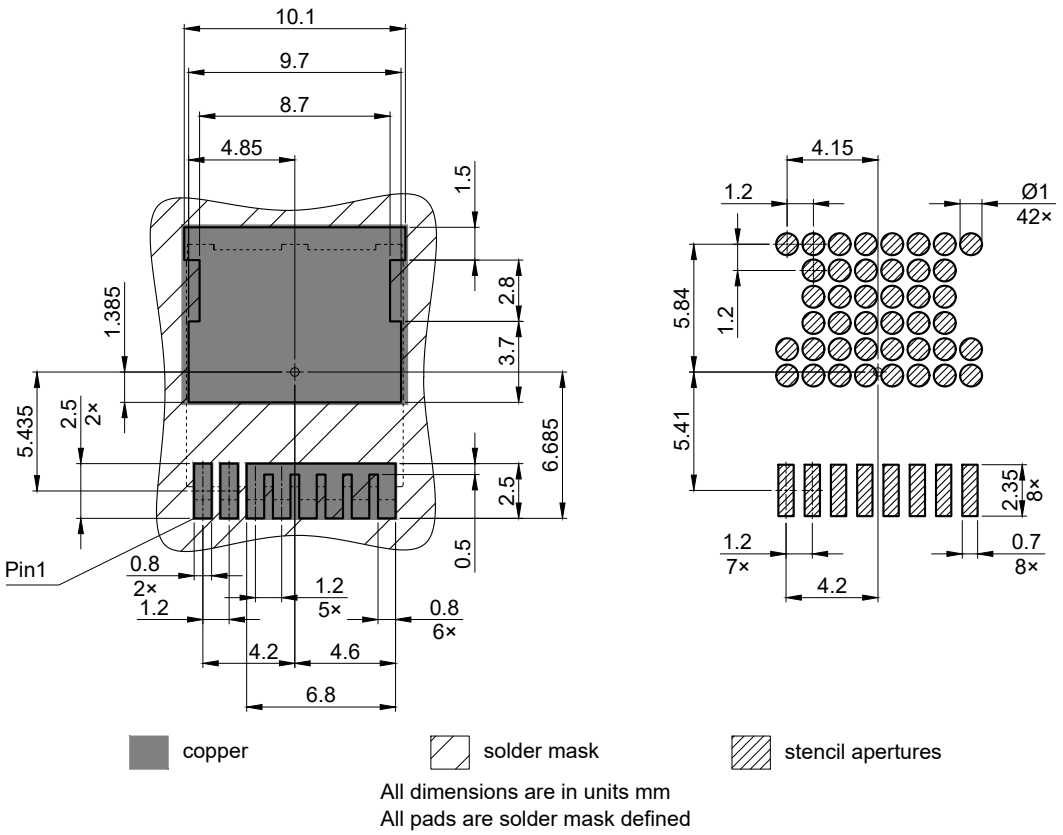


Figure 2 Footprint drawing PG-HSOF-8, dimensions in mm

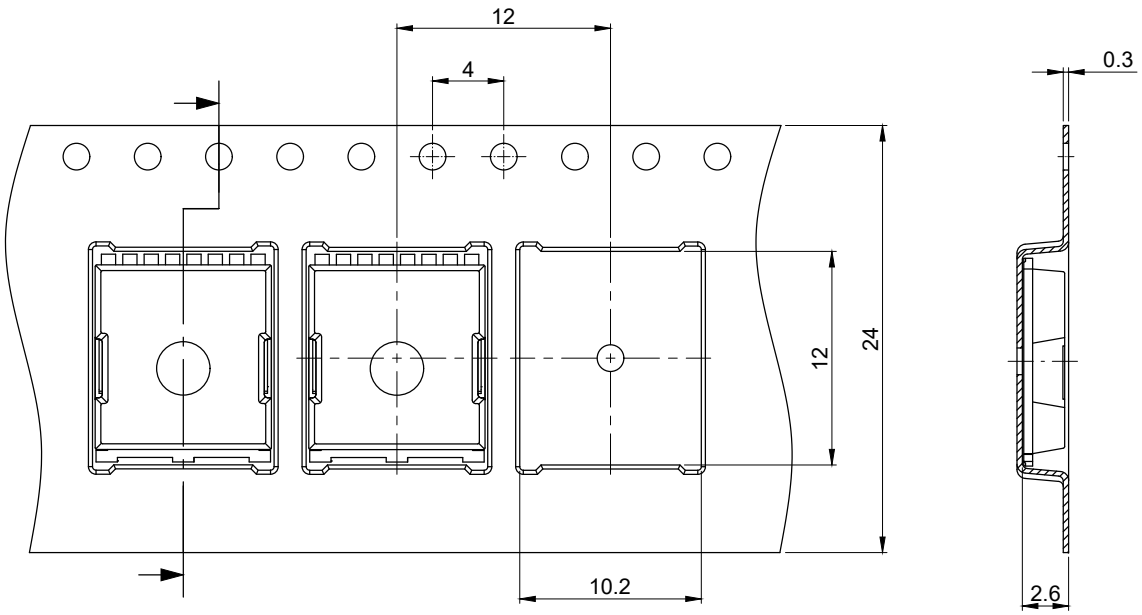


Figure 3 Packaging variant PG-HSOF-8, dimensions in mm

8 Appendix A

Table 12 Related links

- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Webpage
- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Application Note
- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Simulation Model
- IFX Design tools

Revision history

IMT65R010M2H

Revision 2025-01-16, Rev. 2.1

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2024-11-06	Release of final
2.1	2025-01-16	updated continuous reverse drain current

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